Features

- Phase Noise: -169 dBc/Hz @ 10 kHz
- Gain: 14 dB
- Psat: +25 dBm
- Bias Voltage: V_{CC} = +6 V
- Bias Current: I_{CQ} = 100 mA
- 50 Ω Matched Input and Output
- Positive Voltage Only
- Die Size: 3000 x 1400 x 100 µm
- RoHS* Compliant

Applications

- Radar
- Electronic Countermeasures
- Test and Measurement
- Microwave Communication Systems

Description

The MAAL-011161-DIE is an easy to use low phase noise amplifier chip. It operates from 2 - 18 GHz and provides -169 dBc/Hz phase noise, 14 dB gain and +25 dBm P_{SAT}. The input and output are fully matched to 50 Ω with typical return loss >10 dB.

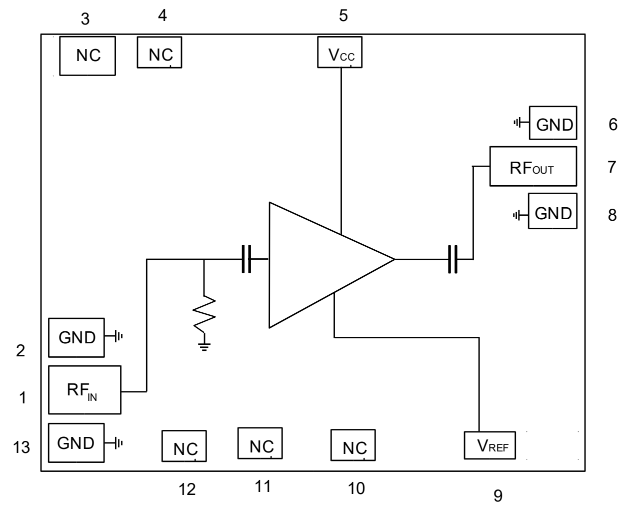
This product is fabricated using a GaAs HBT process which features full passivation for enhanced reliability.

The MAAL-011161-DIE is ideally suited for Radar, Test and Measurement, EW, ECM, and Microwave Communication Systems applications.

Ordering Information

Part Number	Package
MAAL-011161-DIE	Gel Pack

Functional Schematic



Pad Configuration[1]

Pad #	Pad Name	Description
2,6,8,12, 13	GND	DC + RF Ground to Backside Via
1	RF_{IN}	RF Input
3,4,10, 11	NC	Not Connected
5	V_{CC}	Supply Voltage
7	RF_{OUT}	RF Output
9	V_{REF}	Reference Voltage

1. Backside of die must be connected to RF, DC and thermal ground.

* Restrictions on Hazardous Substances, compliant to current RoHS EU directive.

Electrical Specifications: (Based on probed die production data)
Freq. = 2 - 18 GHz, T_A = +25°C, V_{CC} = 6 V, Z_0 = 50 Ω

Parameter	Test Conditions	Units	Min.	Typ.	Max.
Gain	P_{IN} = -10 dBm, 2 GHz P_{IN} = -10 dBm, 10 GHz P_{IN} = -10 dBm, 18 GHz	dB	12.5 12.0 10.0	14.5 14.0 13.5	—
Gain Flatness	—	dB	—	±0.5	—
Gain Variation over Temperature	—	dB/°C	—	0.025	—
Output Power	P_{IN} = +9 dBm, 2 GHz P_{IN} = +9 dBm, 10 GHz P_{IN} = +5.2 dBm, 18 GHz	dBm	18 20 15.5	20 22 17.5	—
Noise Figure	—	dB	—	4.5	—
Input Return Loss	—	dB	—	12	—
Output Return Loss	—	dB	—	10	—
P1dB	10 GHz	dBm	—	21	—
P_{SAT}	10 GHz	dBm	—	25	—
OIP3	10 GHz, -10 dBm P_{IN} per tone	dBm	—	34	—
Phase Noise	10 GHz, P_{SAT} 100 Hz 1 kHz 10 kHz 1 MHz	dBc/Hz	—	 -149 -160 -169 -178	—
Icq	—	mA	—	100	—

Absolute Maximum Ratings[2,3]

Parameter	Absolute Maximum
Input Power	19 dBm
V_{CC}	7.5 V
I_{CC}	270 mA
Junction Temperature[4,5]	+130°C
Operating Temperature	-40°C to +85°C
Storage Temperature	-65°C to +125°C

2. Exceeding any one or combination of these limits may cause permanent damage to this device.
3. MACOM does not recommend sustained operation near these survivability limits.
4. Operating at nominal conditions with $T_J \leq$ +130°C will ensure MTTF > 1 x 10^6 hours.
5. Junction Temperature (T_J) = T_C + Θjc * (V * I)
   Typical thermal resistance (Θjc) = 12.5 °C/W.
   a) For T_C = +25°C,
      T_J = 50.3°C @ 7.5 V, 270 mA
   b) For T_C = +85°C,
      T_J = 110.3°C @ 7.5 V, 270 mA

Maximum Operating Conditions

Parameter	Maximum
Input Power	15 dBm
V_{CC}	7 V
I_{CC}	220 mA
Junction Temperature	+130°C
Operating Temperature	-40°C to +85°C
Storage Temperature	-65°C to +125°C

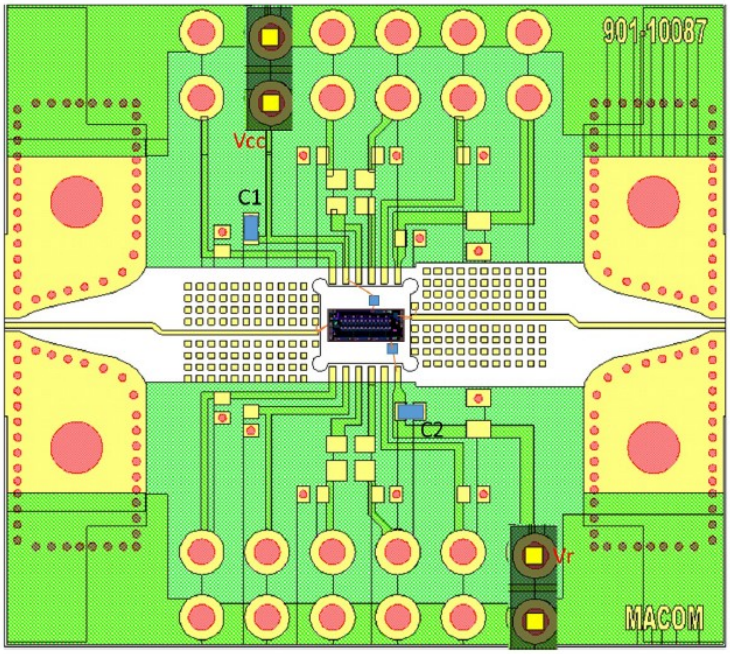
Handling Procedures

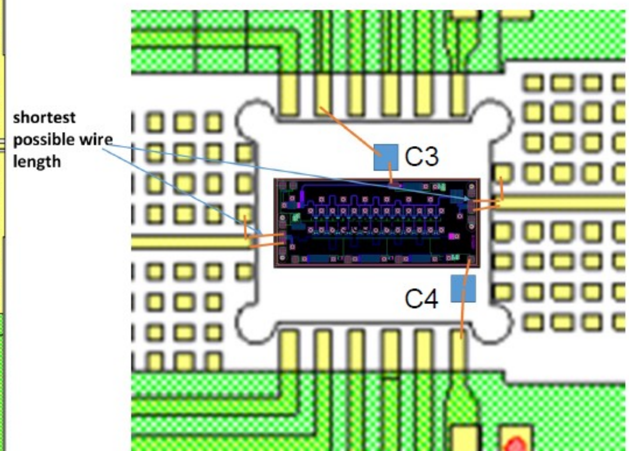
Please observe the following precautions to avoid damage:

Static Sensitivity

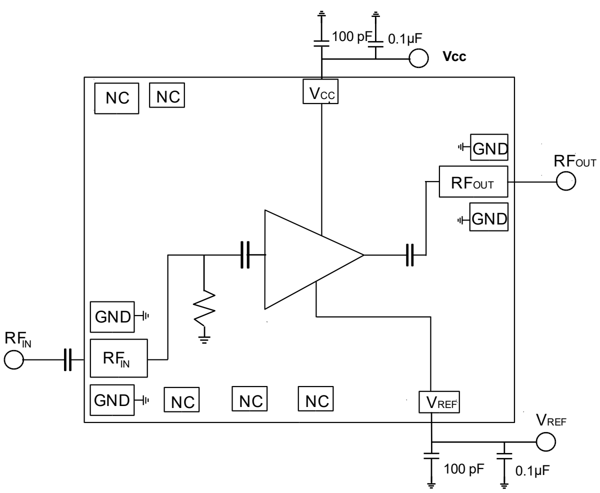
These electronic devices are sensitive to electrostatic discharge (ESD) and can be damaged by static electricity. Proper ESD control techniques should be used when handling these HBM Class 1A, 250 V devices.

PCB Layout





Application Schematic



Operation

To turn-on:

1. Apply +6 V to V_{CC}
2. Starting at 0 V, adjust V_{REF} for target I_{CC}

To turn-off:

1. Set V_{REF} to 0 V
2. Set V_{CC} to 0 V

Evaluation PCB Specifications

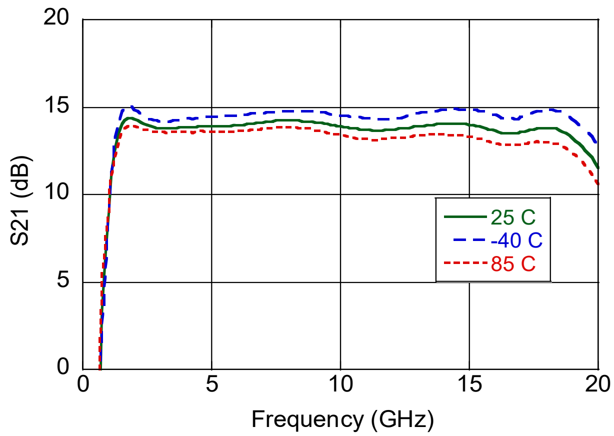
Top Layer: 1/2 oz Copper Cladding, 0.017 mm thickness
Dielectric Layer: Rogers RO4350B 0.101 mm thickness
Bottom Layer: 1/2 oz Copper Cladding, 0.017 mm thickness
Finished overall thickness: 0.135 mm

Parts List

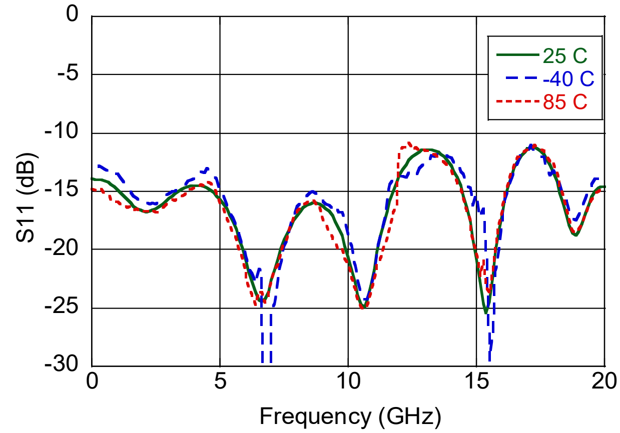
Part	Value	Case Style	MFG	MFG Part #
C3, C4	100 pF	Single Layer	MACOM	MKVC-050100-1453
C1, C2	0.1 µF	0402	KYOCERA	04023C103KAT2A

Typical Performance Curves: V_{CC} = 6 V, I_{CC} = 100 mA

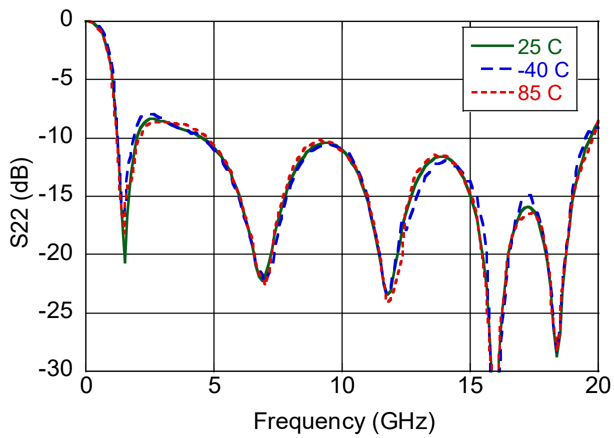
Gain



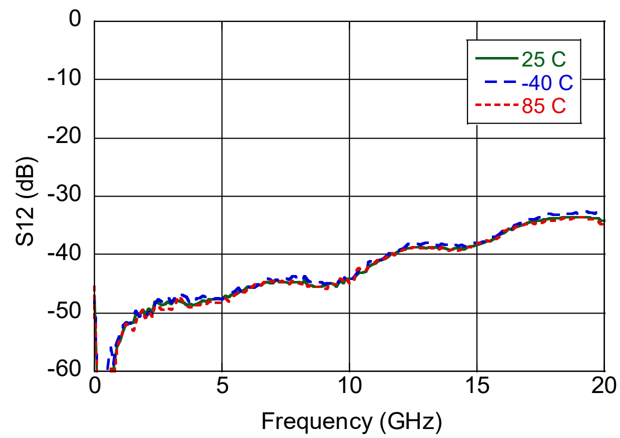
Input Return Loss



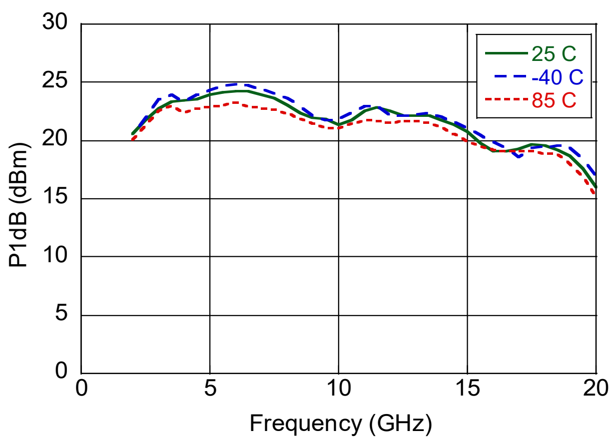
Output Return Loss



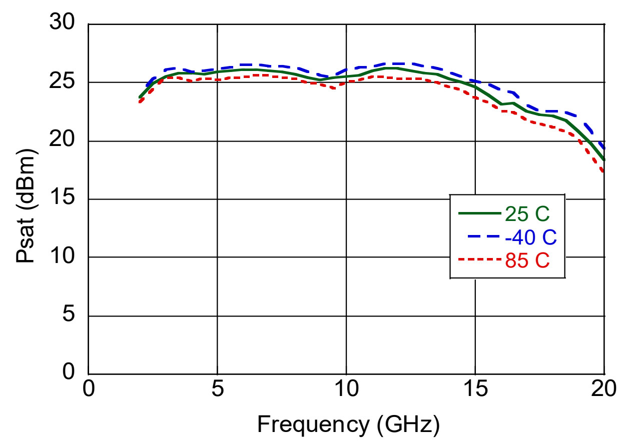
Reverse Isolation



P1dB

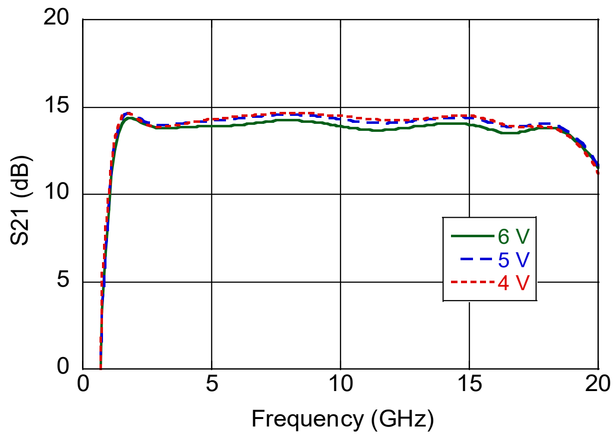


P_{SAT}

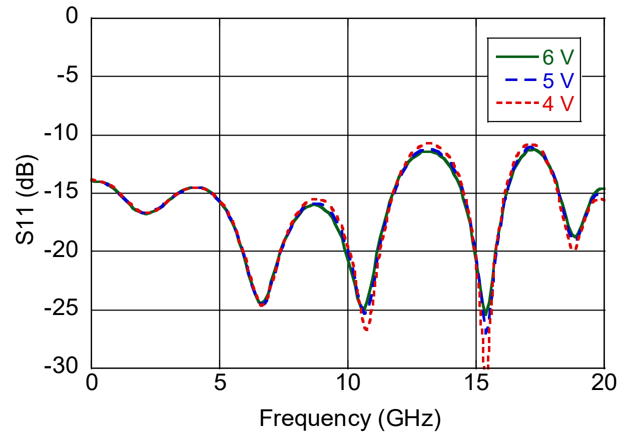


Typical Performance Curves: I_{CC} = 100 mA, +25°C

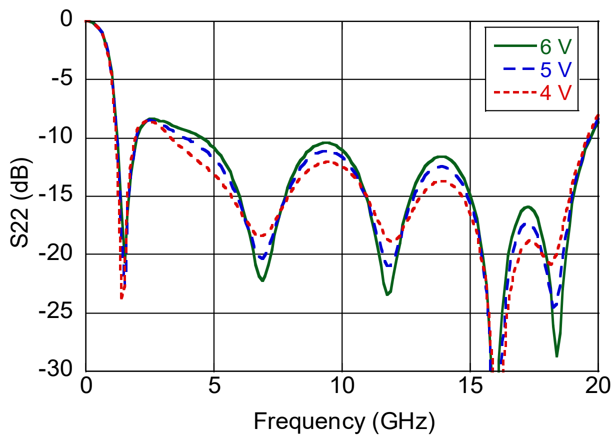
Gain



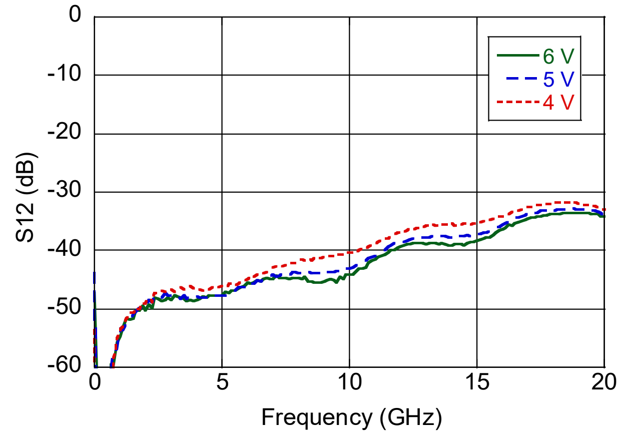
Input Return Loss



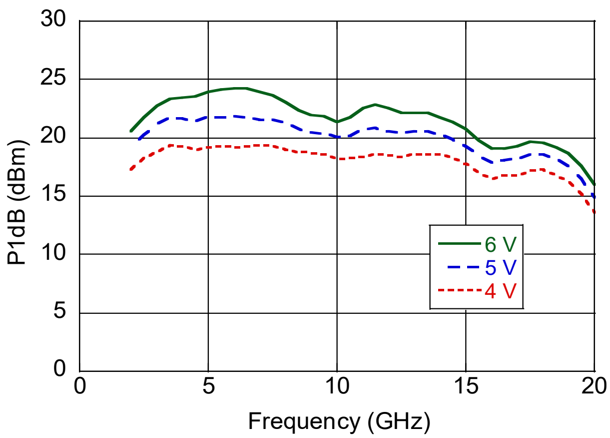
Output Return Loss



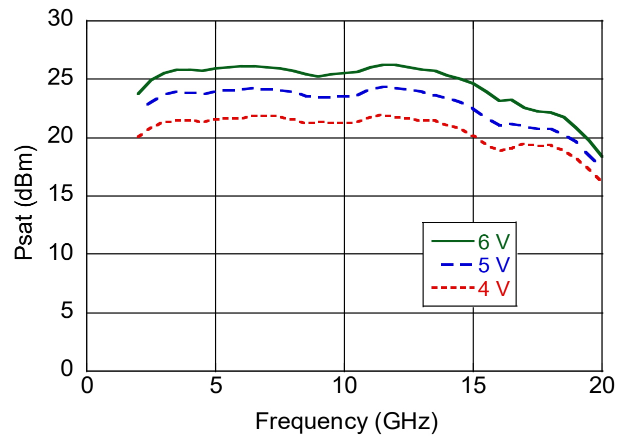
Reverse Isolation



P1dB

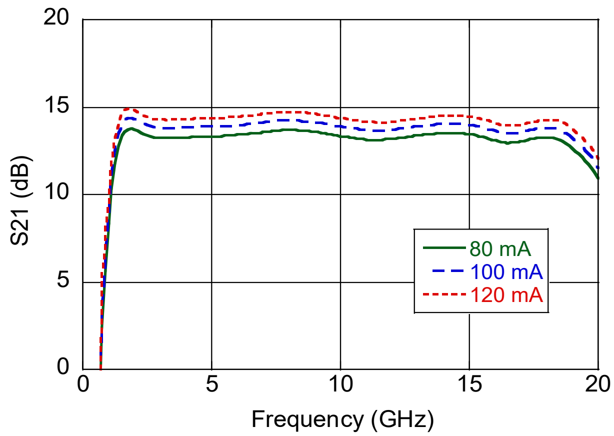


P_{SAT}

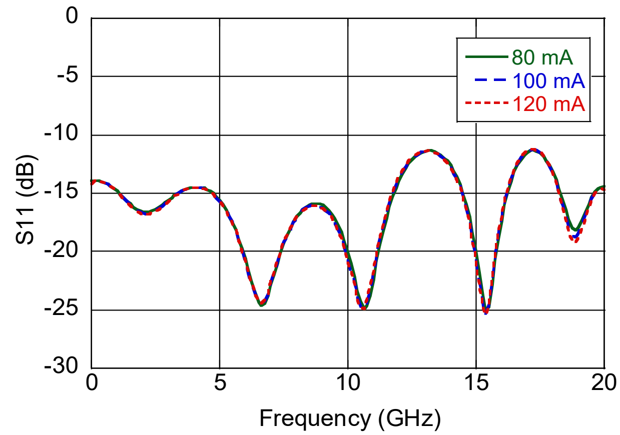


Typical Performance Curves: V_{CC} = 6 V, +25°C

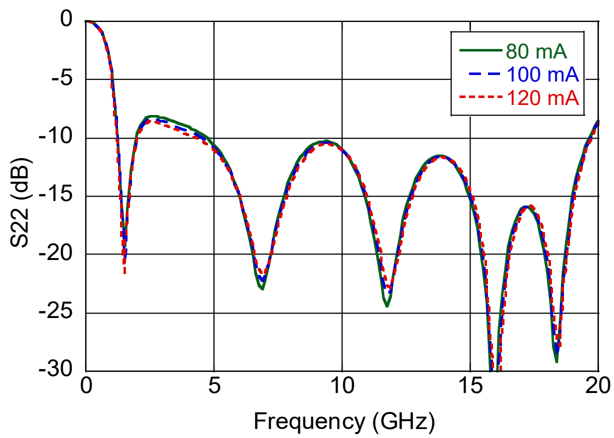
Gain



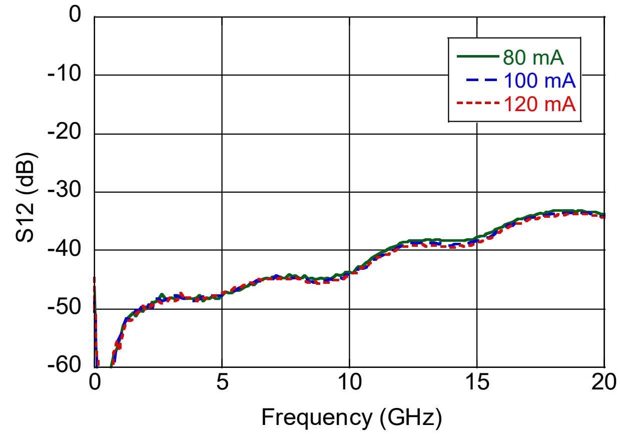
Input Return Loss



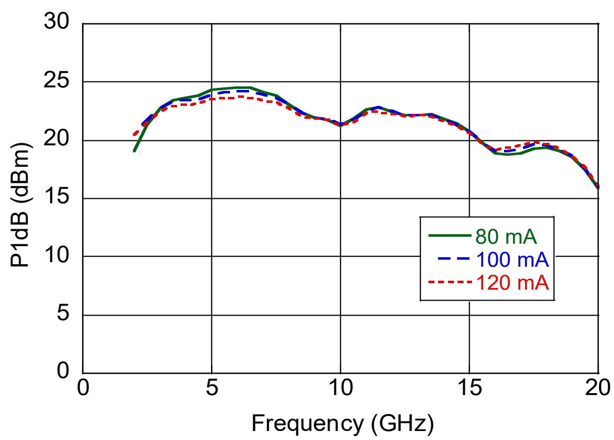
Output Return Loss



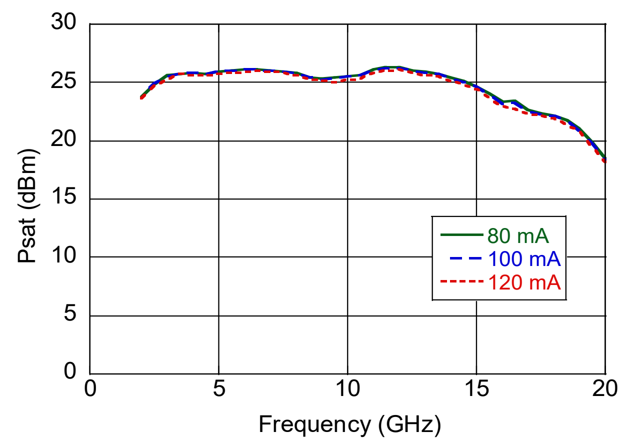
Reverse Isolation



P1dB

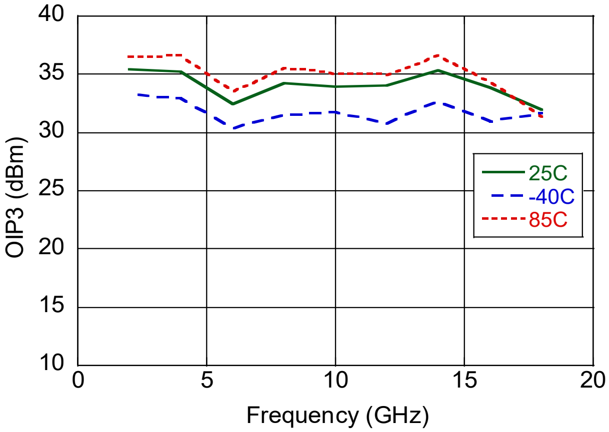


P_{SAT}

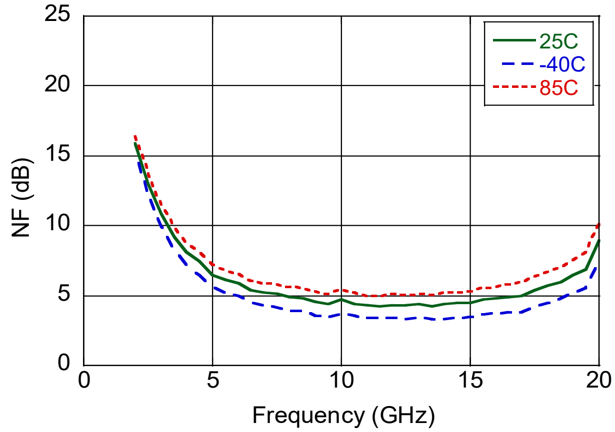


Typical Performance Curves: V_{CC} = 6 V, I_{CC} = 100 mA, +25°C

Output IP3
(10 MHz Tone Spacing, P_{IN} = -10 dBm per tone)



Noise Figure



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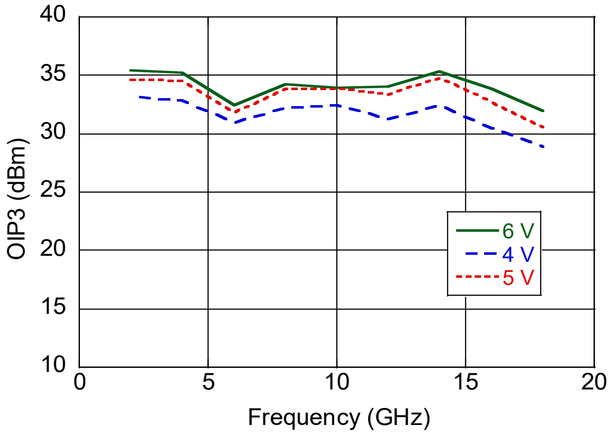
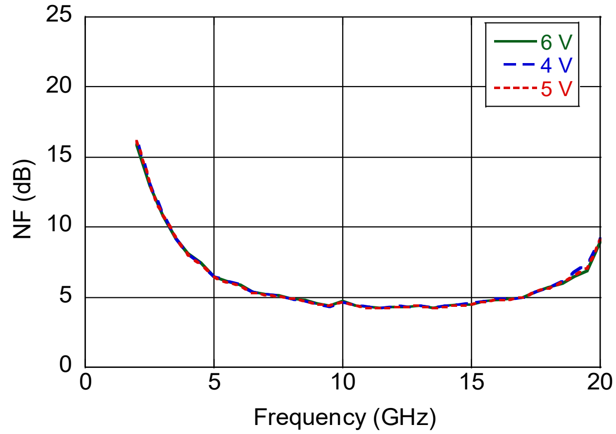
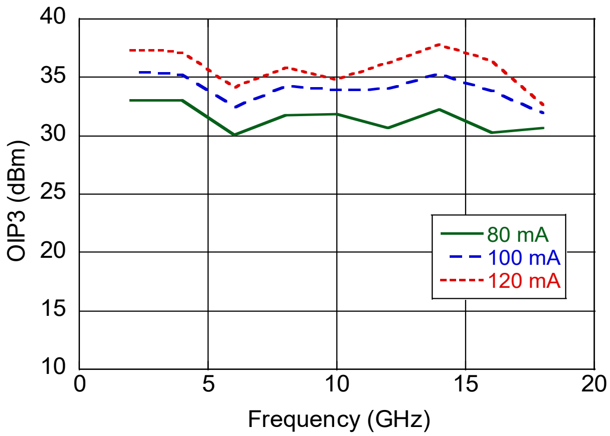
(10 MHz Tone Spacing, P_{IN} = -10 dBm per tone)



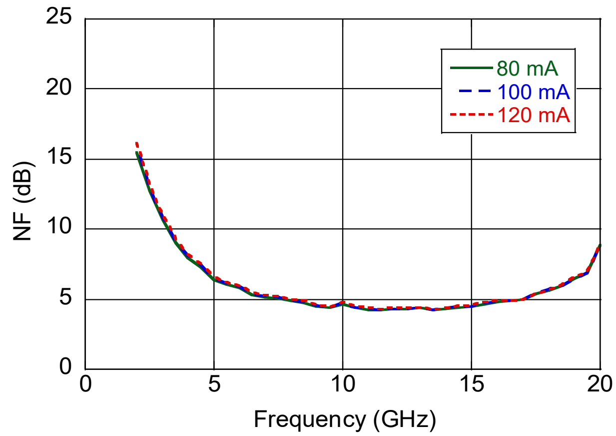
Noise Figure



Output IP3
(10 MHz Tone Spacing, P_{IN} = -10 dBm per tone)

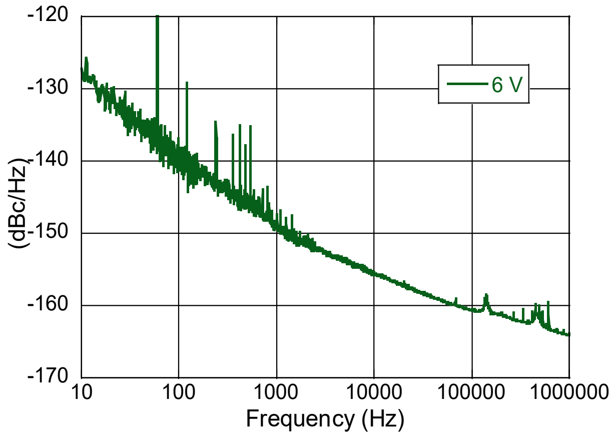


Noise Figure

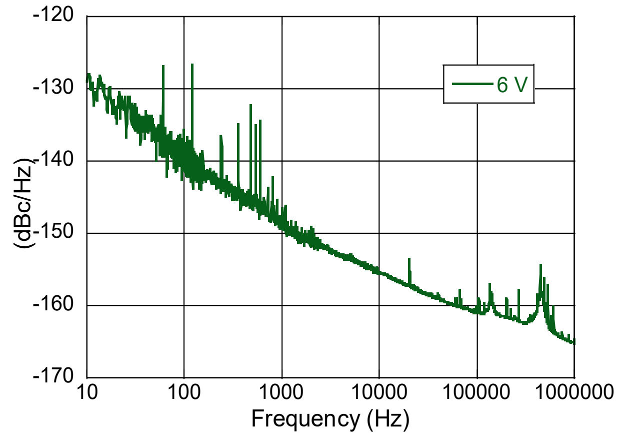


Typical Performance Curves: I_{CC} = 100 mA, +25°C

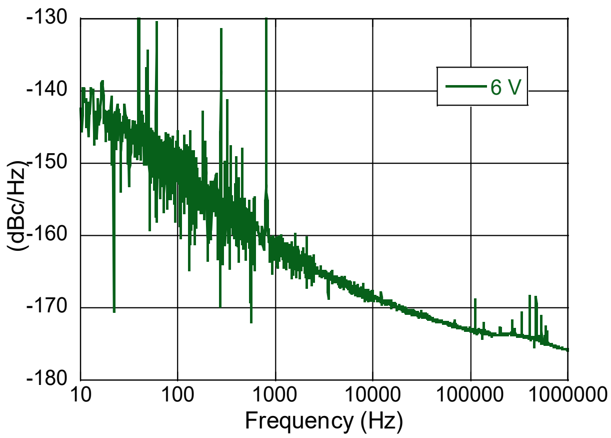
Phase Noise @ 4 GHz, P1dB[6]



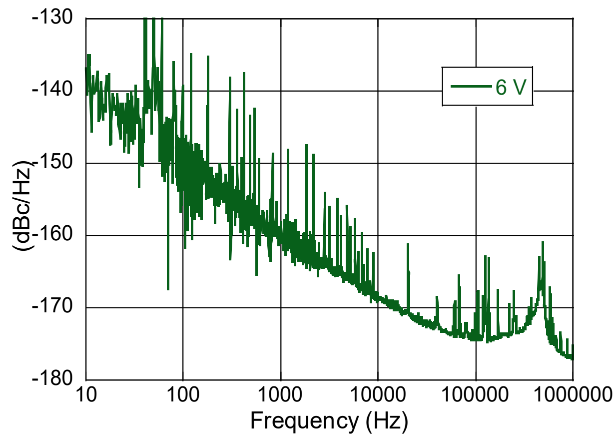
Phase Noise @ 4 GHz, P3dB[6]



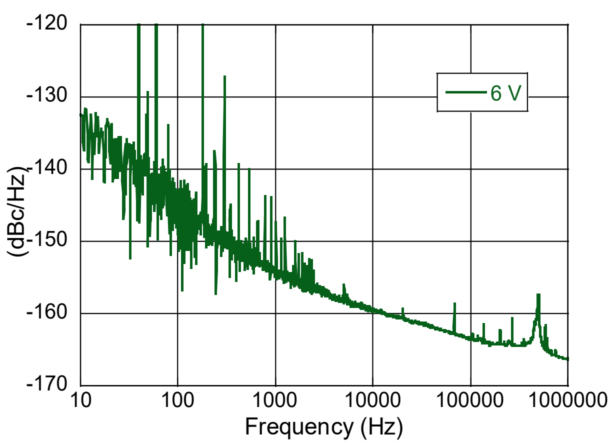
Phase Noise @ 10 GHz, P1dB[6]



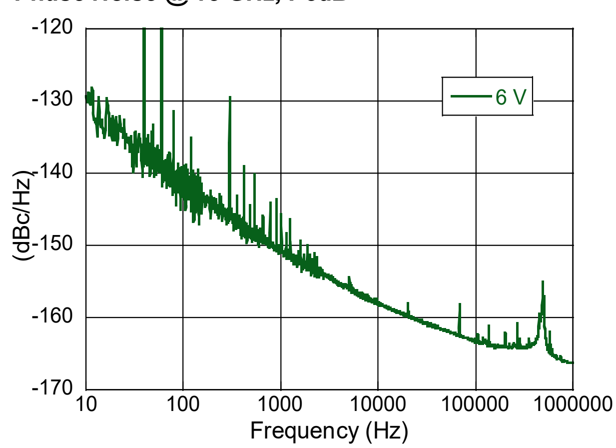
Phase Noise @ 10 GHz, P3dB[6]



Phase Noise @ 18 GHz, P1dB[6]



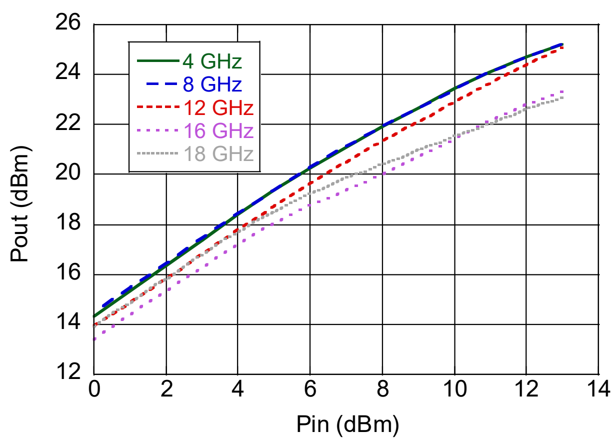
Phase Noise @ 18 GHz, P3dB[6]



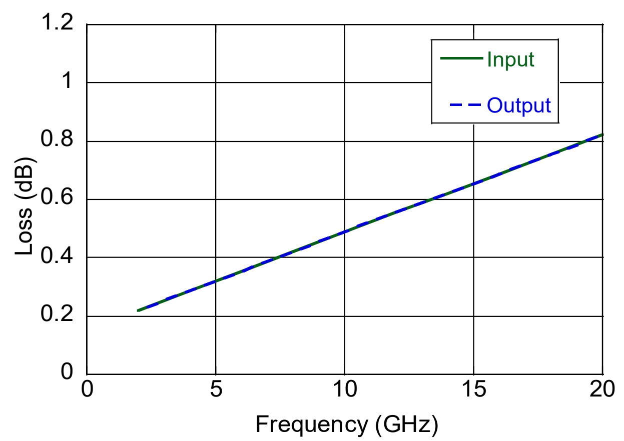
6. The aberration in the phase noise data at approximately 500KHz is due to the test equipment used and not the amplifier itself .

Typical Performance Curves: V_{CC} = 6 V, I_{CC} = 100 mA, +25°C

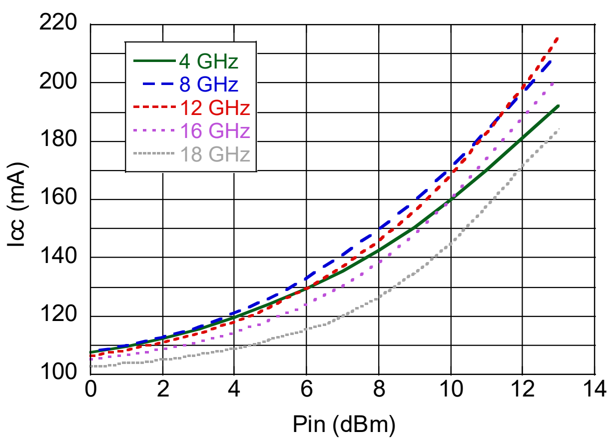
Output Power vs Input Power



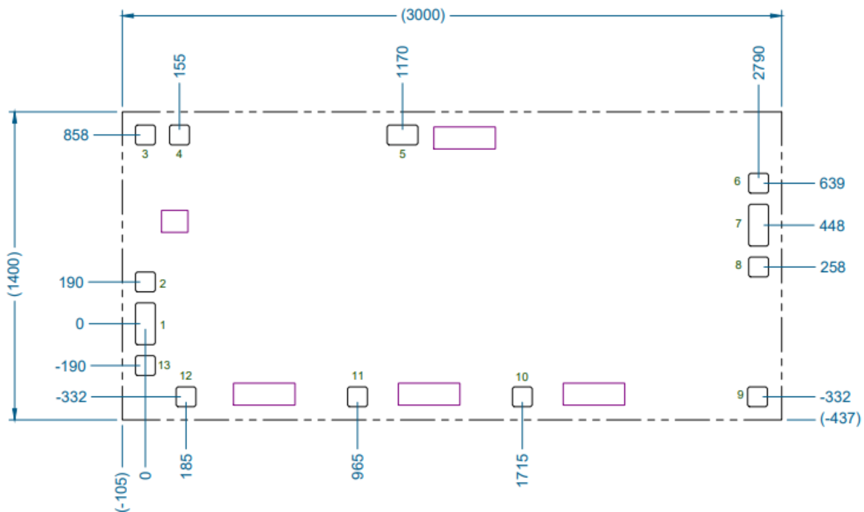
Test Board Loss



Bias Current vs Input Power



MMIC Die Outline



BONDPAD DETAIL		
PAD	SIZE(x)	SIZE(y)
1,7	100	200
2,3,4,6,8,9, 10,11,12,13	100	100
5	150	100

NOTES:
1. UNLESS OTHERWISE SPECIFIED, ALL DIMENSIONS SHOWN ARE µm WITH A TOLERANCE OF ±5µm.
2. DIE THICKNESS IS 100 ±10µm
3. BOND/PAD BACKSIDE METALLIZATION: GOLD
4. DIE SIZE REFLECTS FINAL DIMENSIONS.